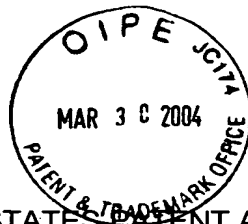


Docket Number: 081468-0307087
Client Reference: P-0395.010-US



PATENT APPLICATION

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In Re the Application of

KLAUS SIMON et al.

Group Art Unit: 1753

Application No.: 10/724,402

Examiner:

Filed: December 1, 2003

Confirmation No.: 8896

For: LITHOGRAPHIC APPARATUS AND DEVICE MANUFACTURING METHOD

INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents
P. O. Box 1450
Alexandria, VA 22313-1450

Sir:

Pursuant to 37 CFR 1.56, the attention of the Patent and Trademark Office is hereby directed to the references listed on the attached PTO-1449. It is respectfully requested that the information be expressly considered during the prosecution of this application, and that the references be made of record therein and appear among the "References Cited" on any patent to issue therefrom. Applicants respectfully request the Examiner return an initialed copy of the enclosed Form PTO-1449 to Applicants with the next Office communication to indicate that the reference(s) has been considered, per MPEP § 609.

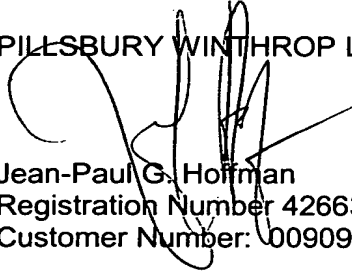
This Information Disclosure Statement is being filed before the mailing date of the first Office Action on the merits in the present application. No certification or fee is required.

U.S. Patent No. 5,610,683, U.S. Published Application No. 2002/041420, Cerrina et al. and Singh-Gasson et al. articles were cited in a counterpart foreign application. An English language version of the foreign search report is attached.

The undersigned respectfully notes that copies of U.S. references are not required in applications filed after June 30, 2003.

Respectfully Submitted,

PILLSBURY WINTHROP LLP


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**INFORMATION DISCLOSURE STATEMENT
BY APPLICANT**

Atty. Dkt. No.	M#	Client Ref.
	307087	P-0395.010-US
Applicant: SIMON <i>et al.</i>		
Appln. No.: 10/724,402		
Filing Date: December 1, 2003		
Examiner: Unknown		Group Art Unit: 1753

Date: March 30, 2004 Page 1 of 3

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	BR	3,648,587	03/1972	Stevens	95	44	
	CR	4,346,164	08/1982	Tabarelli <i>et al.</i>	430	311	
	DR	4,396,705	08/1983	Akeyama <i>et al.</i>	430	326	
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						Enclosed	No	Enclose	No
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	PR	EP 0023231 ✓	02/1981	Europe	Tabarelli <i>et al.</i>	X			
	QR	EP 0418427 ✓	03/1991	Europe	Miyake	X		X	
	RR	EP 1039511 ✓	09/2000	Europe	Murakimi <i>et al.</i>	X		X	
	SR	DD 224448 ✓	07/1985	German	Hesse <i>et al.</i>		X		
	TR	DD 242880 ✓	02/1987	German	Kuch		X		
	UR	FR 2474708 ✓	07/1981	France	Letellier		X		
	VR	JP 62-065326 ✓	03/1987	Japan	Moriuchi	X			
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BBR	M. Switkes <i>et al.</i> , "Immersion Lithography: Optics for the 50 nm Node", 157 Anvers-1, September 4, 2002 ✓			

Examiner Date Considered:

*EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP § 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to Applicant.

FORM PTO-1449 (modified)
To: U.S. Department of Commerce
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Patent and Trademark Office



Atty. Dkt. No.	M#	Client Ref.
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Applicant:	SIMON <i>et al.</i>
Appln. No.:	10/724,402
Filing Date:	December 1, 2003
Examiner:	Unknown
Group Art Unit:	1753

Date: March 30, 2004 Page 2 of 3

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	CR	2002/0041420	04/2002	Garner	359	212	
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	GR						
	HR						
	IR						
	JR						

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							Enclosed	No	Enclose	No
	KR	JP 04-305915	10/1992	Japan	Ozeki <i>et al.</i>		X			
	LR	JP 04-305917	10/1992	Japan	Ozeki <i>et al.</i>		X			
	MR	JP 06-124873	05/1994	Japan	Takahashi		X		X	
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	XR									
	YR									
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BBR	B.J. Lin, "Proximity Printing Through Liquid", IBM Technical Disclosure Bulletin, Vol.20, No. 11B, April 1978, p. 4997				

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INFORMATION DISCLOSURE STATEMENT BY APPLICANT



Applicant: SIMON *et al.*

Appln. No.: 10/724,402

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Examiner: Unknown

Group Art Unit: 1753

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AR						

FOREIGN PATENT DOCUMENTS

Document Number	Date MM/YYYY	Country	Inventor Name	English Abstract	Translation Readily Available
BR				Enclosed	No

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SR	A. Suzuki, "Lithography Advances on Multiple Fronts", EEdesign, EE Times, January 5, 2004				
TR					

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